Dry Developing Process of Molecular Layer Deposited Hf-Based Hybrid Thin Films for EUV Lithography

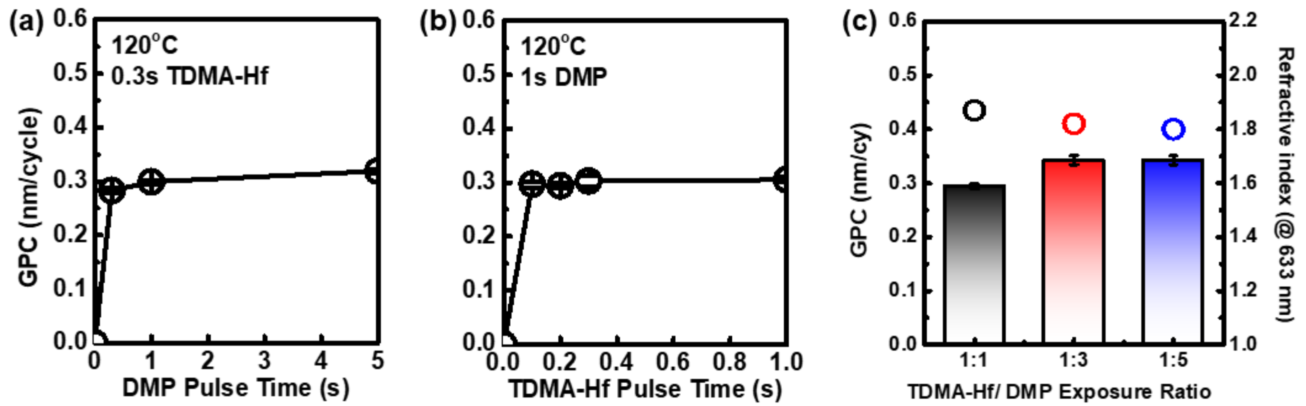

Figure 1. GPC as a function of precursor pulse time, varying (a) DMP pulse time and (b) TDMA-Hf pulse time. (c) GPC and refractive index for samples deposited with different TDMA-Hf / DMP exposure ratios.

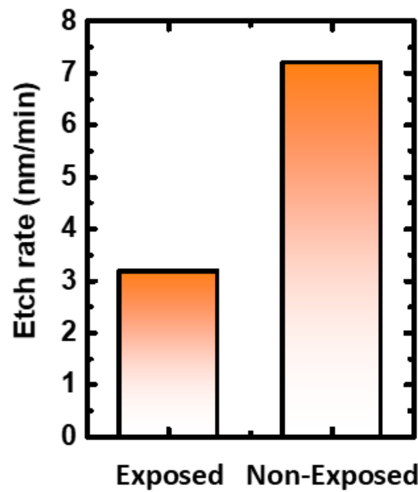

Figure 2. Etch rate comparison between e-beam exposed and non-deposited samples using BCl_3 gas in ICP RIE dry etching process.